

MDL-III-830 /1~30mW

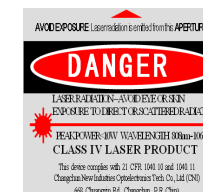
INFRARED DIODE LASER AT 830nm

Infrared diode laser at 830nm is made features of round spot, long lifetime, low cost and easy operating, which is widely used in measurement, spectrum analysis, etc.



SPECIFICATIONS

Wavelength (nm)	830±10
Output power (mW)	>1, 5, 10, ..., 30
Transverse mode	Near TEM ₀₀
Operating mode	CW
Power stability (rms, over 4 hours)	<1%, <3%, <5%
Warm-up time (minutes)	<10
Beam divergence, full angle (mrad)	<1.0
Dimensions of beam at the aperture (mm)	~3.0
Beam height from base plate (mm)	24.8
Operating temperature (°C)	10~35
Power supply (90-264VAC)	PSU-III-FDA
TTL modulation/ Analog modulation	Optional, 2kHz or higher (others on request, up to 30kHz)
Warranty	1 year



MxL-III -830	Dimension	PSU-III-FDA	Dimension
<p>140. 8(L)×73(W)×46. 2(H) mm³, 0.6kg</p>		<p>133 (L) ×130(W) ×65 (H) mm³, 1.2kg</p>	